FIG 1

FIG 2

202 — DETERMINE BIAS AT EACH PITCH THAT MAXIMIZES COMMON PROCESS WINDOW

204 — PERFORM RULE-BASED OPC

206 — PERFORM MODEL-BASED OPC

200

FIG 3A

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FIG 3B

FIG 4

404

402

FIG 5

EXPOSURE DOSE

DEPTH OF FOCUS

FIG 6

FIG 7

Inventor(s): Shinn-Sheng Yu
Serial No.: To Be Assigned
Filed: Herewith
For: Optical Proximity Correction Common Process ... Feature Pitch
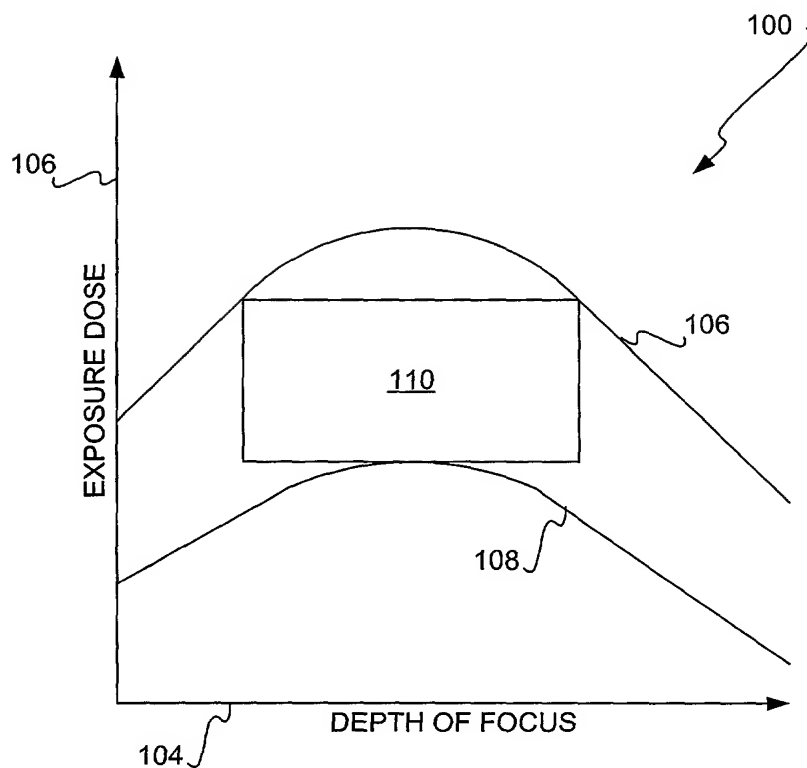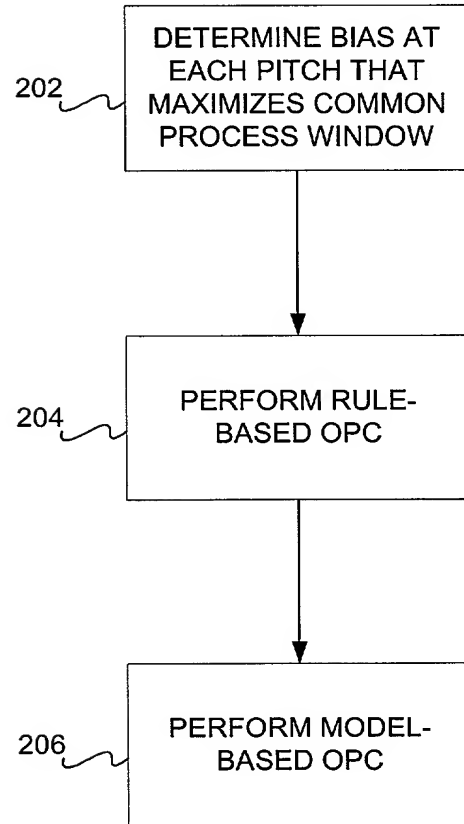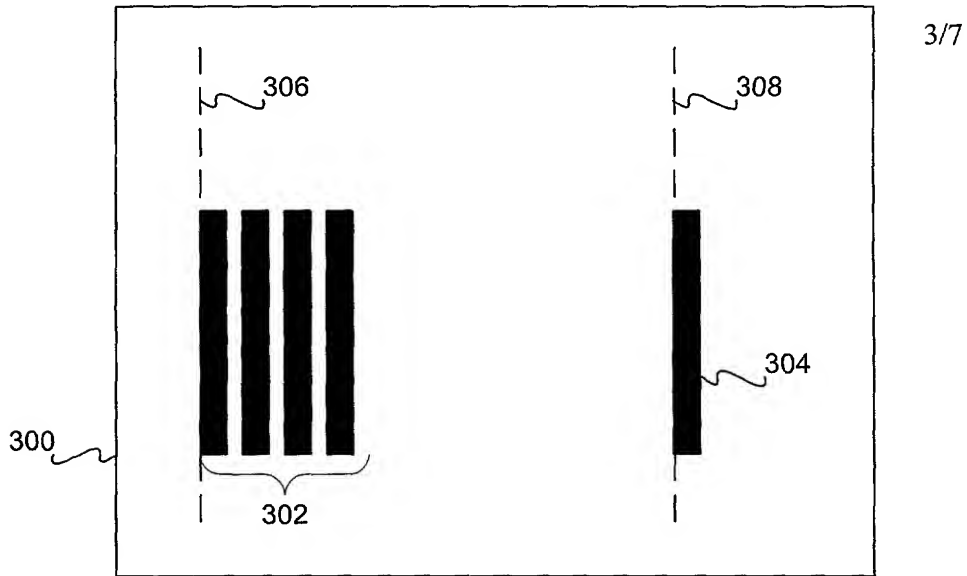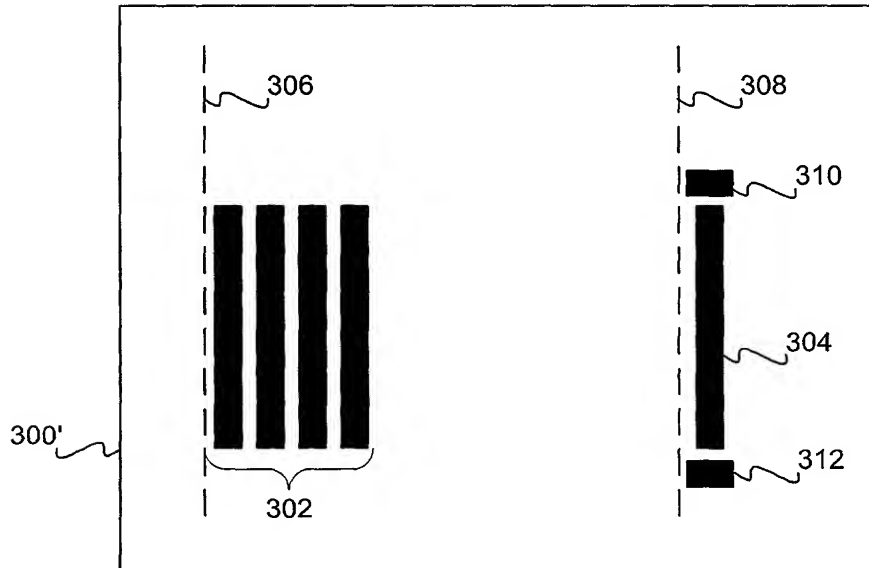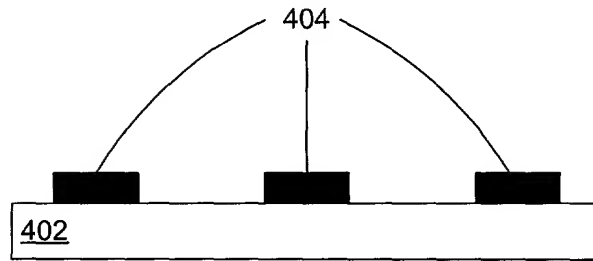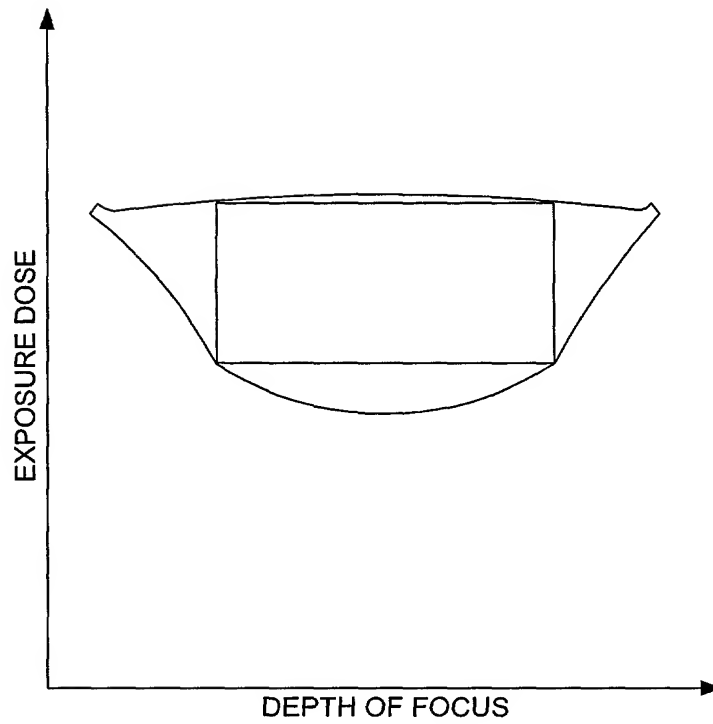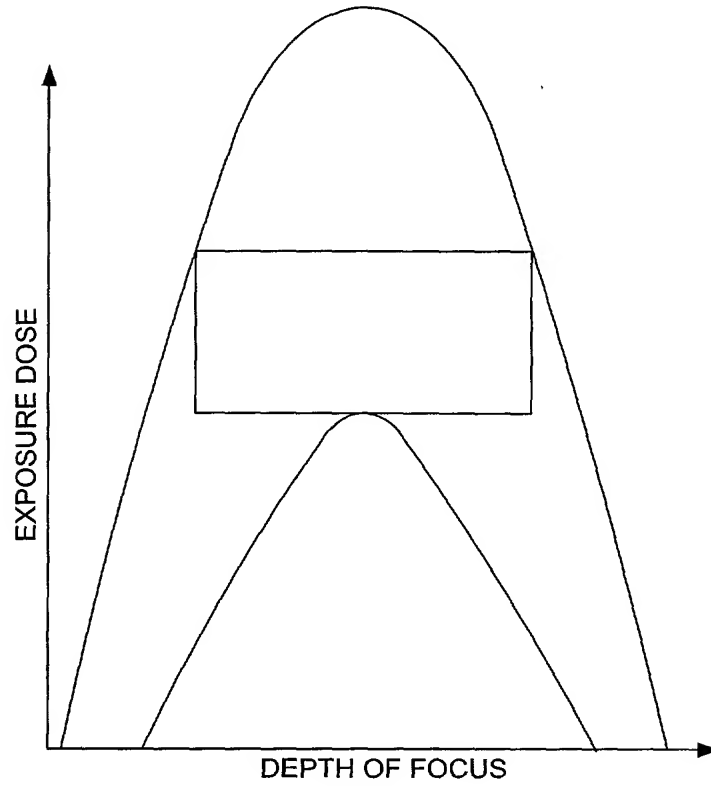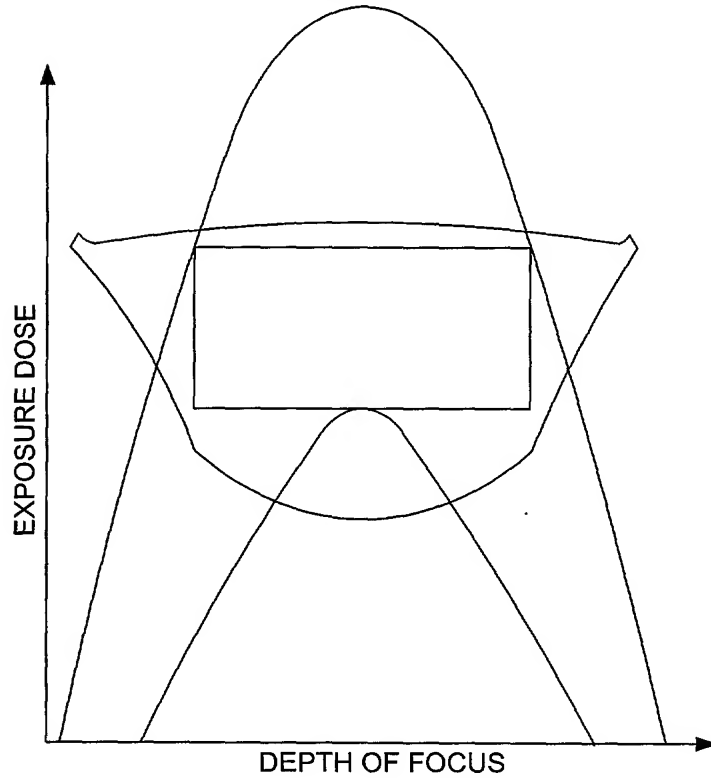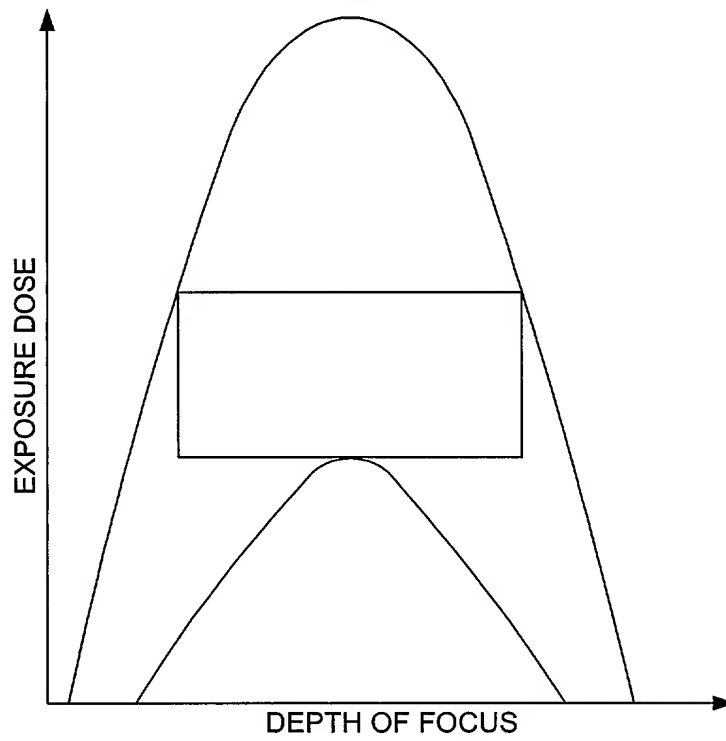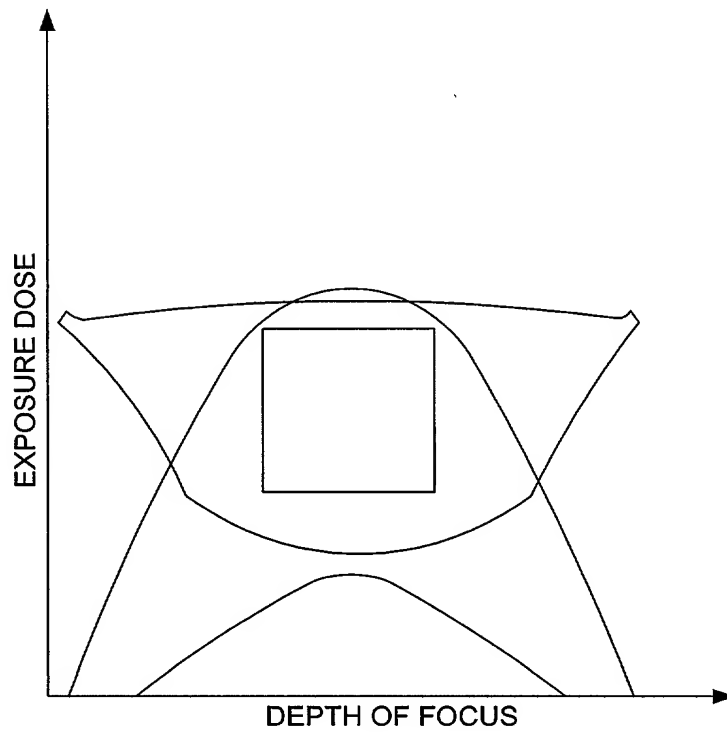Attorney Docket No.: 67,200-515

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FIG 8

EXPOSURE DOSE

DEPTH OF FOCUS

FIG 9

EXPOSURE DOSE

DEPTH OF FOCUS

FIG 10

1002 — POSITION PHOTOMASK OVER WAFER WITH PHOTORESIST LAYER

1004 — EXPOSE WAFER THROUGH PHOTOMASK

1006 — DEVELOP WAFER TO REMOVE EXPOSED PHOTORESIST

1008 — ETCH WAFER WHERE WAFER IS REVEALED THROUGH EXPOSED PHOTORESIST THAT HAS BEEN REMOVED

1010 — REMOVE UNEXPOSED PHOTORESIST

1000